



N-Channel 30-V (D-S), 175°C MOSFET

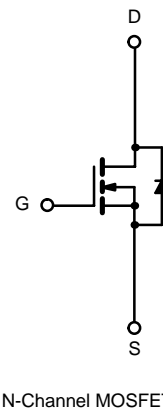
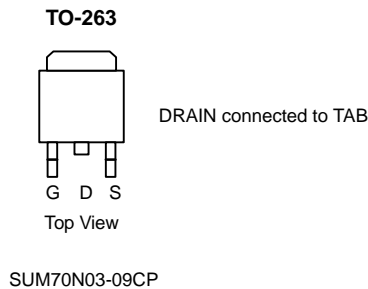
PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0095 @ $V_{GS} = 10$ V	70
	0.014 @ $V_{GS} = 4.5$ V	58

FEATURES

- TrenchFET® Power MOSFET
- Optimized for High- or Low-Side
- New Low Thermal Resistance Package

APPLICATIONS

- DC/DC Converters
- Synchronous Rectifiers



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 10	
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	70
		$T_C = 125^\circ\text{C}$	40
Pulsed Drain Current	I_{DM}	100	A
Avalanche Current	I_{AR}	35	
Repetitive Avalanche Energy ^a	E_{AR}	61 ^b	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25^\circ\text{C}$	93
		$T_A = 25^\circ\text{C}$	3.75
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	$^\circ\text{C}/\text{W}$
Junction-to-Case	R_{thJC}	1.6	

- Notes
- Duty cycle $\leq 1\%$.
 - See SOA curve for voltage derating.
 - When mounted on 1" square PCB (FR-4 material).

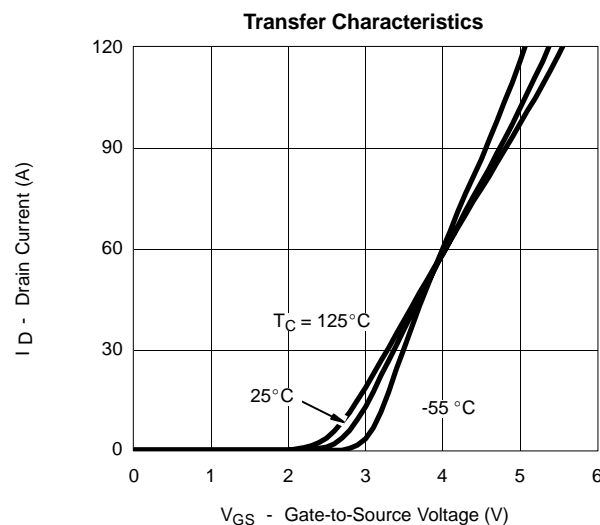
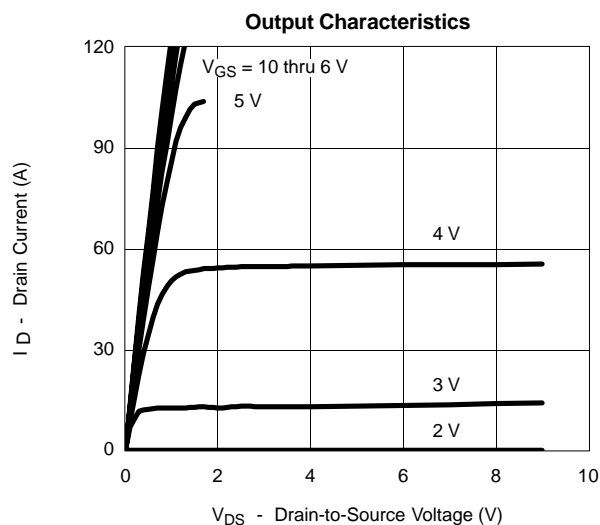
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	μA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 125 °C			250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	100			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0076	0.0095	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.015	
		V _{GS} = 4.5 V, I _D = 20 A		0.0115	0.014	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A	20			S
Dynamic^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		2200		pF
Output Capacitance	C _{oss}			410		
Reverse Transfer Capacitance	C _{rss}			180		
Gate Resistance	R _G			1.5		Ω
Total Gate Charge ^c	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 50 A		31	45	nC
Gate-Source Charge ^c	Q _{gs}			7.5		
Gate-Drain Charge ^c	Q _{gd}			5.0		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 15 V, R _L = 0.3 Ω I _D = 50 A, V _{GEN} = 10 V, R _G = 2.5 Ω		9	15	ns
Rise Time ^c	t _r			80	120	
Turn-Off Delay Time ^c	t _{d(off)}			22	35	
Fall Time ^c	t _f			8	12	
Source-Drain Diode Ratings and Characteristic (T_C = 25 °C)						
Pulsed Current	I _{SM}				100	A
Diode Forward Voltage ^b	V _{SD}	I _F = 50 A, V _{GS} = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		35	70	ns

Notes

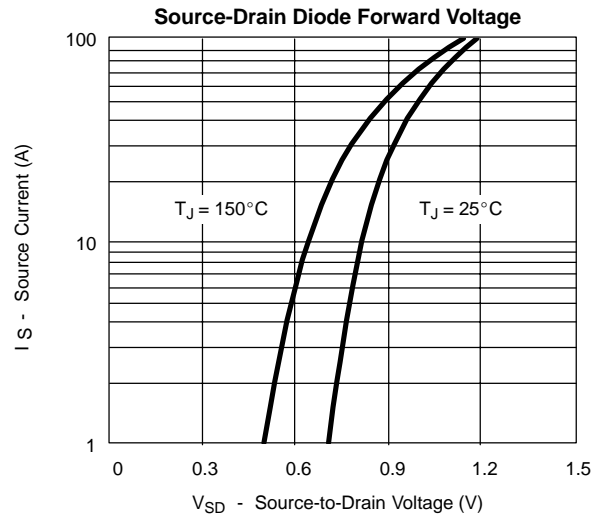
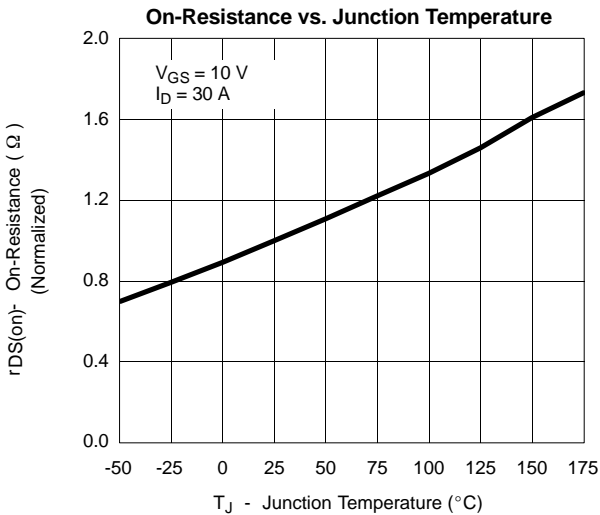
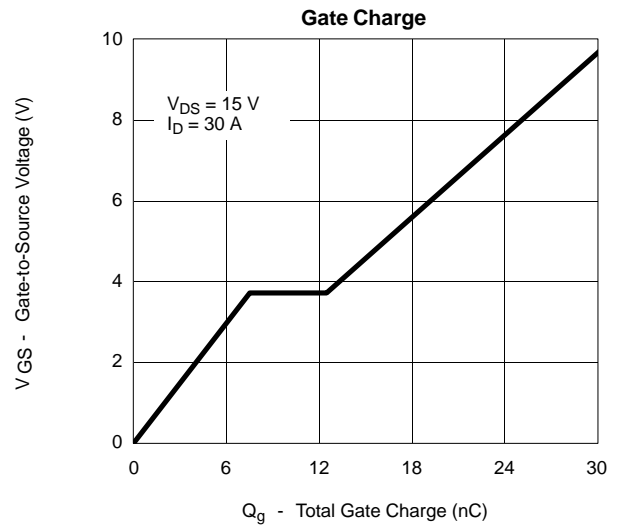
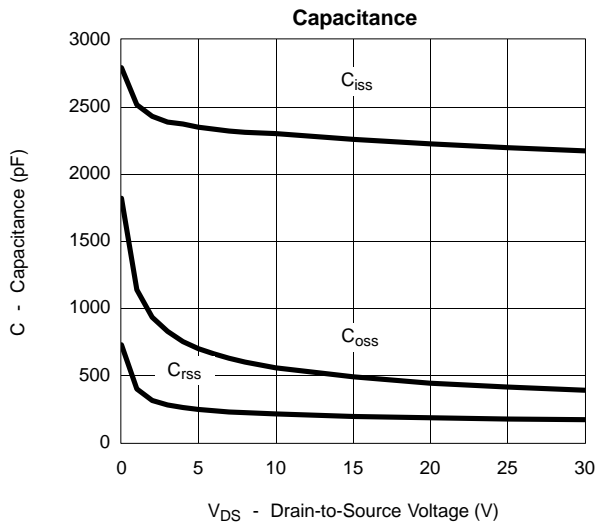
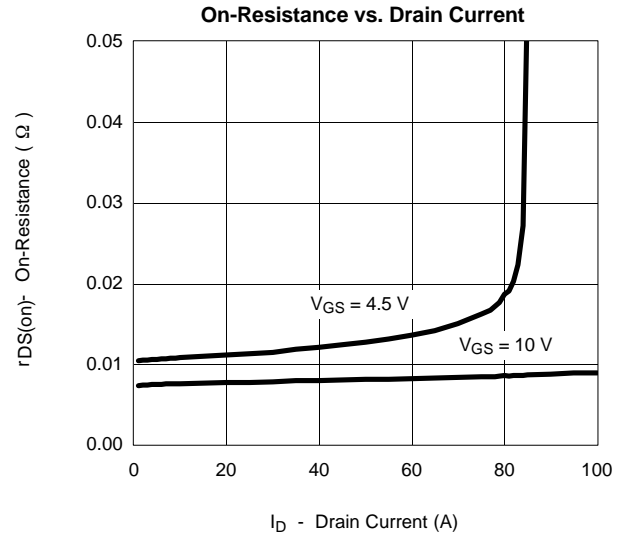
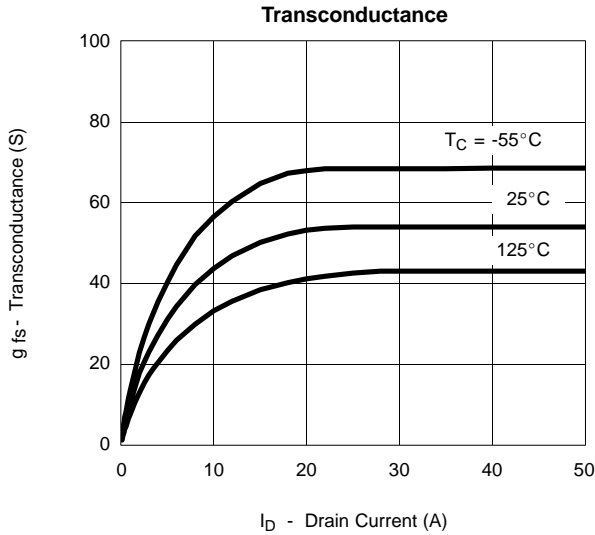
- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Independent of operating temperature.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



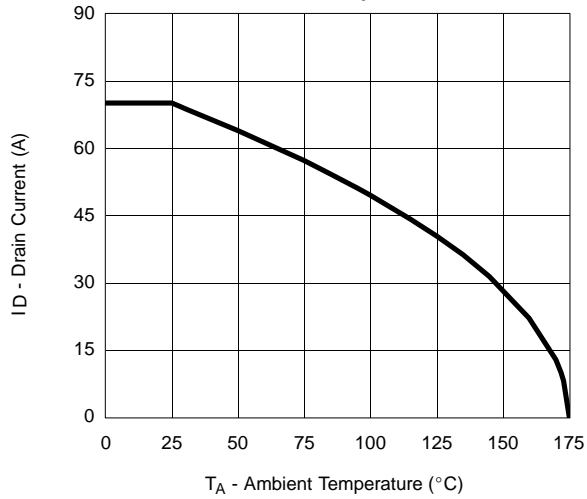


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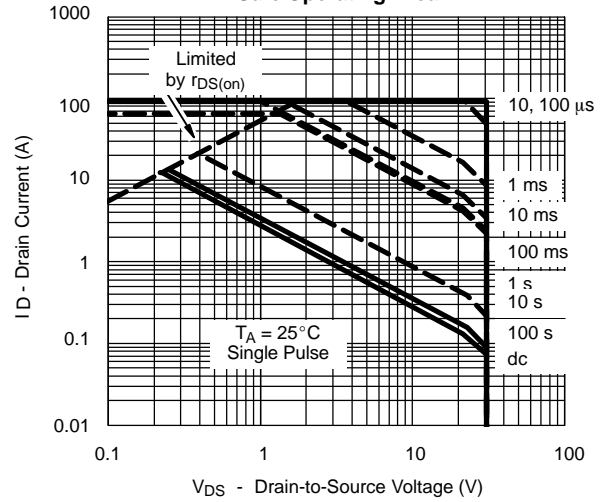


THERMAL RATINGS

Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

